

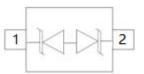




SD05C THRU SD24C TVS ARRAY



Schematic & Pin Configuration



Description

The SDxxC TVS diodes are designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebook computers, and PDA's. They offer superior electrical characteristics such as lower clamping voltage and no device degradation when compared to MLVs. The SDxxC series TVS diodes are designed to protect sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events.

The SDxxC is in a SOD-323 package and will protect one unidirectional line. These devices will fit on the same PCB pad area as an 0805 MLV device. They give the designer the flexibility to protect one line in applications where arrays are not practical. Additionally, it may be "sprinkled" around the board in applications where board space is at a premium.

They may be used to meet the ESD immunity requirements of IEC 61000-4-2, Level 4 (±15kV air, ±8Kv contact discharge).

Application

- Cell Phone Handsets and Accessories
- Microprocessor based equipment
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops, and Servers
- Portable Instrumentation
- Pagers Peripherals

Mechanical Characteristics

- SOD-323 package
- Molding compound flammability rating: UL 94V-0
- Marking : Marking code
 Packaging : Tape and Reel

Features

- 350 Watts peak pulse power (tp = 8/20 μ s)
- Transient protection for data lines to IEC 61000-4-2 (ESD) \pm 15kV (air), \pm 8kV (contact) IEC 61000-4-4 (EFT) 40A (5/50ns) IEC 61000-4-5 (Lightning) 24A (8/20 μ s)
- Small package for use in portable electronics
- Suitable replacement for MLV's in ESD protection applications
- Protects one I/O or power line
- Low clamping voltage
- Working voltages: 5V and 24V
- Low leakage current
- Solid-state silicon-avalanche technology
- Terminals finish: 100% Pure Tin







Maximum Ratings@T_A=25° C unless otherwise specified

Parameter	Symbol	Value	Units
Peak Pulse Power (tp =8/20 μ s)	P _{PK}	350	W
Peak Pulse Current (tp =8/20 μ s)	I PP	24	Α
ESD Voltage (HBM Waveform per IEC 61000-4-2)	V_{ESD}	30	KV
Lead Soldering Temperature	T∟	260(10 sec.)	°C
Operating Temperature	TJ	-55 to + 125	$^{\circ}\!\mathbb{C}$
Storage Temperature	T _{STG}	-55 to + 150	$^{\circ}$

Electrical Characteristics@TA=25°C unless otherwise specified

SD05C	Marking code	D05C				
Characteristics	Symbol	Condition	Min.	Тур.	Max.	Units
Reverse Stand-Off Voltage	V _{RWM}	-	-	-	5	V
Reverse Breakdown Voltage	V _{BR}	@ I _t =1mA	6	-	-	V
Reverse Leakage Current	I _R	@V _{RWM} = 5V, T = 25 ℃	-	-	10	μA
Clamping Voltage	Vc	@I _{PP} = 5A, tp=8/20µs	-	-	9.8	V
Clamping Voltage	Vc	@I _{PP} = 24A, tp=8/20µs	-	-	14.5	V
Junction Capacitance	C _j	$@V_R = 0V, f_{SIG} = 1MHz$	-	-	200	pF

SD12C	Marking code	D12C				
Characteristics	Symbol	Condition	Min.	Тур.	Max.	Units
Reverse Stand-Off Voltage	V _{RWM}	-	-	-	12	V
Reverse Breakdown Voltage	V _{BR}	@ I _t =1mA	13.3	-	-	V
Reverse Leakage Current	I _R	@V _{RWM} = 12V, T = 25 ℃	_	-	1	μA
Clamping Voltage	Vc	@I _{PP} = 5A, tp=8/20µs	-	-	19	V
Clamping Voltage	Vc	@I _{PP} = 15A, tp=8/20µs	-	-	24	V
Junction Capacitance	C _j	$@V_R = 0V, f_{SIG} = 1MHz$	-	-	100	pF

SD15C	Marking code	D15C				
Characteristics	Symbol	Condition	Min.	Тур.	Max.	Units
Reverse Stand-Off Voltage	V _{RWM}	-	-	-	15	V
Reverse Breakdown Voltage	V _{BR}	@ I _t =1mA	16.7	-	-	V
Reverse Leakage Current	I _R	@V _{RWM} = 15V, T = 25 ℃	-	-	1	μA
Clamping Voltage	Vc	@I _{PP} = 5A, tp=8/20µs	-	-	24	V
Clamping Voltage	Vc	@I _{PP} = 12A, tp=8/20µs	-	-	29	V
Junction Capacitance	Cj	$@V_R = 0V, f_{SIG} = 1MHz$	-	-	75	pF

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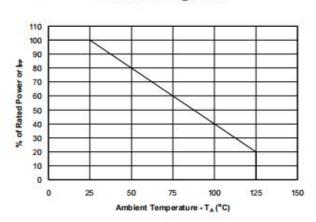
SD18C	Marking code	D18C				
Characteristics	Symbol	Condition	Min.	Тур.	Max.	Units
Reverse Stand-Off Voltage	V_{RWM}	-	-	-	18	V
Reverse Breakdown Voltage	V_{BR}	@ I _t =1mA	20	-	24	V
Reverse Leakage Current	I _R	@V _{RWM} = 18V, T = 25 ℃	-	-	1	μΑ
Clamping Voltage	Vc	@I _{PP} = 1A, tp=8/20µs	-	-	29	V
Clamping Voltage	Vc	@I _{PP} = 9A, tp=8/20µs	-	-	40	V
Junction Capacitance	C _j	$@V_R = 0V, f_{SIG} = 1MHz$	-	-	60	pF

SD24C	Marking code	D24C				
Characteristics	Symbol	Condition	Min.	Typ.	Max.	Units
Reverse Stand-Off Voltage	V _{RWM}	-	-	-	24	V
Reverse Breakdown Voltage	V_{BR}	@ I _t =1mA	26.7	-	-	V
Reverse Leakage Current	I _R	@V _{RWM} = 24V, T = 25 ℃	-	-	1	μΑ
Clamping Voltage	Vc	@I _{PP} = 5A, tp=8/20µs	-	-	40	V
Clamping Voltage	Vc	@I _{PP} = 8A, tp=8/20µs	-	-	44	V
Junction Capacitance	C _i	$@V_R = 0V, f_{SIG} = 1MHz$	-	-	50	pF

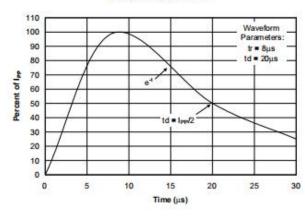
Ratings and Characteristics Curves

Non-Repetitive Peak Pulse Power vs. Pulse Time 10 10 10 10 10 10 10 10 100 100 Pulse Duration - tp (µs)

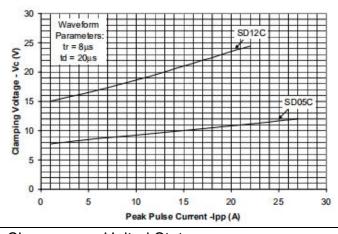
Power Derating Curve



Pulse Waveform



Clamping Voltage vs. Peak Pulse Current



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Ordering Information

Device	Package	Shipping
SD05C THRU SD24C	SOD-323 (Pb-Free)	3000pcs / reel

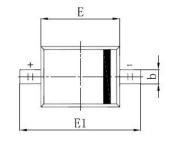
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

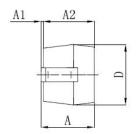
Marking Diagram

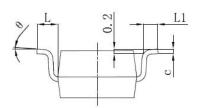


Marking code = D05C

Mechanical Dimensions SOD-323

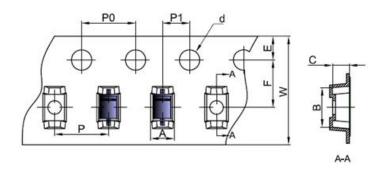






OVMDOL	Millim	Millimeters In		ches	
SYMBOL	MIN.	MAX.	MIN.	MAX.	
Α	-	1.000	-	0.039	
A1	0.000	0.100	0.000	0.004	
A2	0.800	0.900	0.031	0.035	
b	0.250	0.350	0.010	0.014	
С	0.080	0.150	0.003	0.006	
D	1.200	1.400	0.047	0.055	
Е	1.600	1.800	0.063	0.071	
E1	2.500	2.700	0.098	0.106	
L	0.475 REF.		0.019 REF.		
L1	0.250	0.400	0.010	0.016	
θ	0°	8°	0°	8°	

Carrier Tape Specification SOD-323



SYMB	Millimeters			
OL	Min.	Max.		
В	2.85	2.95		
С	1.20	1.30		
d	1.40	1.60		
E	1.65	1.85		
F	3.40	3.60		
Р	3.90	4.10		
P0	3.90	4.10		
P1 1.90		2.10		
W	7.90	8.30		

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SD05C THRU SD24C



Technical Data Data Sheet N2250, Rev. A





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